Orbital Stark effect and quantum confinement transitio

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Citation Report

#	Article	IF	Citations
1	Single dopants learn their place. Nature Nanotechnology, 2010, 5, 100-101.	15.6	3
2	<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msup><mml:mi>D</mml:mi><mml:mo>â^'</mml:mo></mml:msup></mml:mrow></mml:math>ce in uniaxially stressed Si and in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>Si</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>SiO</mml:mtext></mml:mrow></mml:msub></mml:mrow></mml:math> wells. Physical Review B, 2010, 82, .	1.1	0
3	On the nuclear magnetic resonance frequency of phosphorus donor atom in a silicon-based quantum computer. Journal of Applied Physics, 2010, 108, .	1.1	3
4	Coherent transport through a double donor system in silicon. Applied Physics Letters, 2010, 96, 072110.	1.5	9
5	Heterointerface effects on the charging energy of the shallow<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msup><mml:mi>D</mml:mi><mml:mo>â^'</mml:mo></mml:msup></mml:mrow></mml:math>grou state in silicon: Role of dielectric mismatch. Physical Review B, 2010, 82, .	1.1	26
6	Single-electron transfer between two donors in nanoscale thin silicon-on-insulator field-effect transistors. Applied Physics Letters, 2010, 97, 262101.	1.5	24
7	Resonant tunnelling features in quantum dots. Nanotechnology, 2010, 21, 274018.	1.3	47
8	Coherent electron transport by adiabatic passage in an imperfect donor chain. Physical Review B, 2010, 82, .	1.1	20
9	Electrically Addressing a Molecule-Like Donor Pair in Silicon: An Atomic Scale Cyclable Full Adder Logic. Journal of Physical Chemistry C, 2010, 114, 20380-20386.	1.5	10
10	Intervalley coupling for interface-bound electrons in silicon: An effective mass study. Physical Review B, 2011, 84, .	1.1	60
11	Lifetime-Enhanced Transport in Silicon due to Spin and Valley Blockade. Physical Review Letters, 2011, 107, 136602.	2.9	22
12	Single dopants in semiconductors. Nature Materials, 2011, 10, 91-100.	13.3	385
13	Atom devices based on single dopants in silicon nanostructures. Nanoscale Research Letters, 2011, 6, 479.	3.1	66
14	Phosphorus Î´-doped silicon: mixed-atom pseudopotentials and dopant disorder effects. Nanotechnology, 2011, 22, 065701.	1.3	34
15	Stark tuning of the charge states of a two-donor molecule in silicon. Nanotechnology, 2011, 22, 225202.	1.3	12
16	Electronic structure of realistically extended atomistically resolved disordered Si:P<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Î´</mml:mi></mml:math>-doped layers. Physical Review B, 2011, 84, .	1.1	44
17	Engineered valley-orbit splittings in quantum-confined nanostructures in silicon. Physical Review B, 2011, 83, .	1.1	32
18	Strong Stark effect in electroluminescence from phosphorous-doped silicon-on-insulator metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2011, 98, .	1.5	5

#	Article	IF	Citations
19	Electric field reduced charging energies and two-electron bound excited states of single donors in silicon. Physical Review B, 2011, 84, .	1.1	26
20	A hybrid double-dot in silicon. New Journal of Physics, 2012, 14, 023050.	1.2	11
21	Exchange-coupled dopants in Si quantum dots. Applied Physics Letters, 2012, 101, 093108.	1.5	5
22	Impact of the valley degree of freedom on the control of donor electrons near a Si/SiO2interface. Physical Review B, 2012, 86, .	1.1	10
23	Stark effect of donor binding energy in a self-assembled GaAs quantum dot subjected to a tilted electric field. Physics Letters, Section A: General, Atomic and Solid State Physics, 2012, 376, 2712-2716.	0.9	24
24	Engineering Independent Electrostatic Control of Atomic-Scale (â^¼4 nm) Silicon Double Quantum Dots. Nano Letters, 2012, 12, 4001-4006.	4.5	31
25	Detection of a Large Valley-Orbit Splitting in Silicon with Two-Donor Spectroscopy. Physical Review Letters, 2012, 108, 206812.	2.9	48
26	Silicon quantum electronics. Reviews of Modern Physics, 2013, 85, 961-1019.	16.4	892
27	Wave Function Control over a Single Donor Atom. Nano Letters, 2013, 13, 1476-1480.	4.5	28
28	Selection rules for angular-resolved photoionization of single P donor atom in silicon. , 2013, , .		0
29	Acoustic-phonon-assisted quantum control of qubit states near the Si/SiO2 interface. Physica B: Condensed Matter, 2013, 427, 5-11.	1.3	0
30	Effect of a perpendicular magnetic field on the shallow donor states near a semiconductor-metal interface. Physical Review B, 2013, 87, .	1.1	1
31	Coherent Coupling of Two Dopants in a Silicon Nanowire Probed by Landau-Zener-StÃ¼ckelberg Interferometry. Physical Review Letters, 2013, 110, 136802.	2.9	65
32	Spin-Lattice Relaxation Times of Single Donors and Donor Clusters in Silicon. Physical Review Letters, 2014, 113, 246406.	2.9	27
33	Hyperfine Stark effect of shallow donors in silicon. Physical Review B, 2014, 90, .	1.1	41
34	Circuit-quantum electrodynamics with direct magnetic coupling to single-atom spin qubits in isotopically enriched 28Si. AIP Advances, 2014, 4, .	0.6	28
35	Electronic states and wavefunctions of diatomic donor molecular ions in silicon: multi-valley envelope function theory. Journal of Physics Condensed Matter, 2014, 26, 065302.	0.7	12
36	Valley blockade and multielectron spin-valley Kondo effect in silicon. Physical Review B, 2015, 92, .	1.1	15

#	Article	IF	Citations
37	Multivalley envelope function equations and effective potentials for phosphorus impurity in silicon. Physical Review B, 2015, 92, .	1.1	12
38	Second-Harmonic Coherent Driving of a Spin Qubit in a Si/SiGe Quantum Dot. Physical Review Letters, 2015, 115, 106802.	2.9	30
39	Electric-field-assisted formation of an interfacial double-donor molecule in silicon nano-transistors. Scientific Reports, 2015, 5, 17377.	1.6	4
40	The coupled atom transistor. Journal of Physics Condensed Matter, 2015, 27, 154206.	0.7	2
41	Valley-enhanced fast relaxation of gate-controlled donor qubits in silicon. Nanotechnology, 2016, 27, 314002.	1.3	17
42	Highly tunable exchange in donor qubits in silicon. Npj Quantum Information, 2016, 2, .	2.8	45
43	Resonant tunneling spectroscopy of valley eigenstates on a donor-quantum dot coupled system. Applied Physics Letters, 2016, 108, 152102.	1.5	6
44	A computational workflow for designing silicon donor qubits. Nanotechnology, 2016, 27, 424002.	1.3	3
45	Dynamics of a single-atom electron pump. Scientific Reports, 2017, 7, 44371.	1.6	8
46	Electronic states and valley-orbit coupling in linear and planar molecules formed by coupled P donors in silicon. Physical Review B, 2017, 95, .	1.1	7
47	Probing the Quantum States of a Single Atom Transistor at Microwave Frequencies. ACS Nano, 2017, 11, 2444-2451.	7.3	19
48	Two-electron states of a group-V donor in silicon from atomistic full configuration interactions. Physical Review B, 2018, 97, .	1.1	18
49	Donor binding energies in a curved two-dimensional electron system. Applied Surface Science, 2020, 508, 145195.	3.1	13
50	Stark shift of hydrogenic and non-hydrogenic donor impurity excited states in parabolic quantum dot: Under the effect of electric field and temperature. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 118, 113882.	1.3	5
51	Novel characterization of dopant-based qubits. MRS Bulletin, 2021, 46, 616-622.	1.7	4
52	Theory and Simulations of Controlled Electronic States Bound to a Single Dopant in Silicon. , 2013, , .		0
53	Single-Donor Transport Spectroscopy in Ultimate Silicon Transistors. , 2013, , .		0
54	Orbital Structure and Transport Characteristics of Single Donors. , 2013, , .		0

#	Article	IF	Citations
55	Optimisation of electron spin qubits in electrically driven multi-donor quantum dots. Npj Quantum Information, 2022, 8, .	2.8	1